# 2SB1438

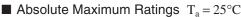
## Silicon PNP epitaxial planar type

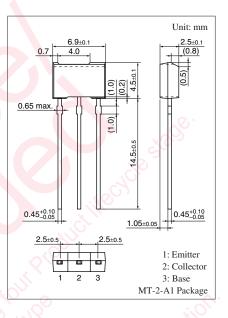
For low-frequency power amplification

#### Features

- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$
- Large collector-emitter voltage (Base open)  $V_{CEO}$
- Allowing supply with the radial taping

Absolute Maximum Hatings $T_a = 25$ C						
Parameter	Symbol	Rating	Unit			
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-100	V			
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-100	V			
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-5	V			
Collector current	I <sub>C</sub>	-2	А			
Peak collector current	I <sub>CP</sub>	-3	А			
Collector power dissipation *	P <sub>C</sub>	1	W			
Junction temperature	Tj	150	°C			
Storage temperature	T <sub>stg</sub>	-55 to +150	°C			





Note) \*: Print circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, \ I_{\rm E} = 0$	-100	2		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$	-100			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *2	$V_{CE} = -2 V, I_C = -200 mA$	120		340	
	h <sub>FE2</sub> *1	$V_{CE} = -2 V, I_C = -1 A$	60			
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_{\rm C} = -1 \text{ A}, I_{\rm B} = -50 \text{ mA}$		- 0.17	- 0.30	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_{\rm C} = -1$ A, $I_{\rm B} = -50$ mA		- 0.85	-1.20	V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		90		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		70	90	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

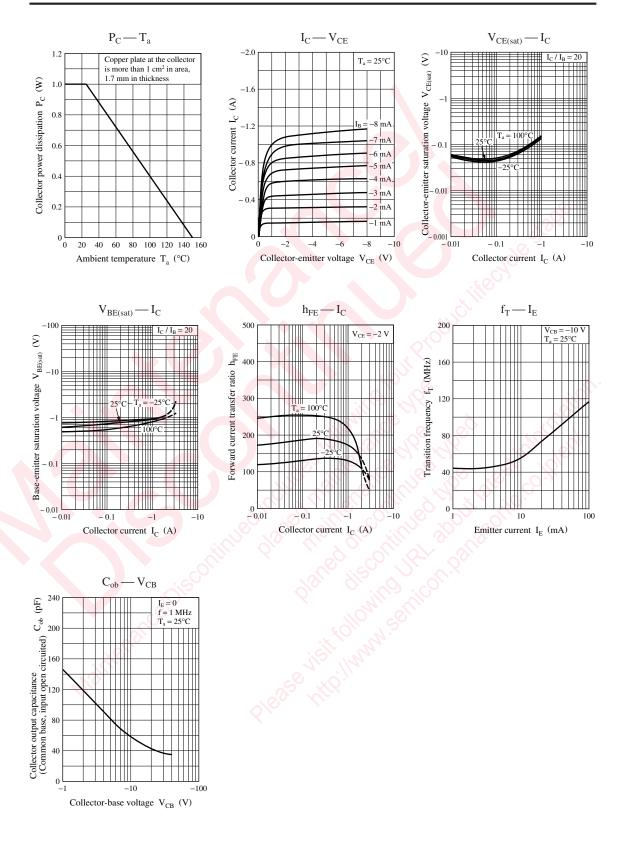
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2. \*1: Pulse measurement

\*2: Rank classification Rank P

Rank	Р	Q
$h_{\rm FE1}$	120 to 240	170 to 340

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